

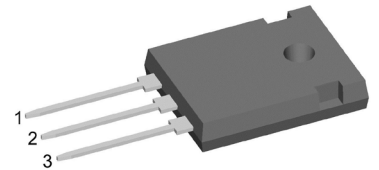
SiC Schottky Diode

$$V_{RRM} = 2 \times 1200 \text{ V}$$

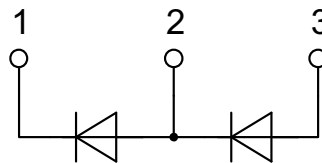
$$I_{FAV} = 12.5 \text{ A}$$

Ultra fast switching
 Zero reverse recovery
 Phase leg

Part number
DCG10P1200HR



Backside: isolated
 E72873



Features / Advantages:

- Ultra fast switching
- Zero reverse recovery
- Zero forward recovery
- Temperature independent switching behavior
- Positive temperature coefficient of forward voltage
- $T_{VJM} = 175^{\circ}\text{C}$

Applications:

- Solar inverter
- Uninterruptible power supply (UPS)
- Welding equipment
- Switched-mode power supplies
- Medical equipment
- High speed rectifier

Package: ISO247

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Backside: DCB ceramic
- Reduced weight
- Advanced power cycling

Disclaimer Notice

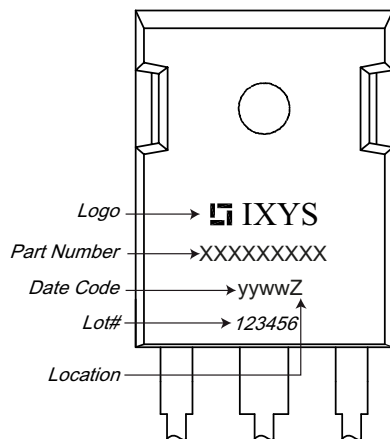
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SiC Diode (per diode)				Ratings				
Symbol	Definitions	Conditions		min.	typ.	max.		
V _{RSM}	max. non-repetitive reverse blocking voltage					1200	V	
V _{RRM}	max. repetitive reverse blocking voltage	T _{VJ} = 25°C				1200	V	
I _R	reverse current	V _R = V _{RRM}	T _{VJ} = 25°C T _{VJ} = 175°C		30 55	250 350	μA μA	
V _F	forward voltage	I _F = 10 A	T _{VJ} = 25°C		1.5	1.8	V V	
		I _F = 20 A						
		I _F = 10 A	T _{VJ} = 175°C		2.2	3.0	V V	
		I _F = 20 A						
I _{FAV}	average forward current	T _C = 80°C	rectangular, d = 0.5 T _{VJ} = 175°C			12.5	A A	
		T _C = 100°C				11.0		
I _{F25}	forward current	based on typ. V _{F0} and r _F		T _C = 25°C		22	A	
I _{F80}				T _C = 80°C		17	A	
I _{F100}				T _C = 100°C		15	A	
I _{FSM}	max forward surge current	t = 10 ms, half sine (50 Hz) t _p = 10 μs, pulse	T _{VJ} = 25°C V _R = 0V			750	A A	
V _{F0}	threshold voltage	for power loss calculation	T _{VJ} = 125°C 175°C		0.77 0.69		V V	
r _F	slope resistance		T _{VJ} = 125°C 175°C		107 133	mΩ mΩ		
Q _C	total capacitive charge		V _R = 800 V, I _F = 10A dI/dt = 200 A/μs	T _{VJ} = 25°C		52	nC	
C	total capacitance	V _R = 0 V V _R = 400 V V _R = 800 V	T _{VJ} = 25°C, f = 1 MHz		755 45 38		pF pF pF	
R _{thJC}	thermal resistance junction to case	with heatsink compound; IXYS test setup			2.2	1.9	K/W K/W	
R _{thJH}	thermal resistance junction to heatsink							

Package ISO247				Ratings			
Symbol	Definitions	Conditions		min.	typ.	max.	
I _{RMS}	RMS current	per terminal				70	A
T _{stg}	storage temperature			-40		150	°C
T _{op}	operation temperature			-40		150	°C
T _{VJ}	virtual junction temperature			-40		175	°C
Weight					6		g
M _D	mounting torque			0.8		1.2	Nm
F _C	mounting force with clip			40		120	N
d _{Spp/App}	creepage distance on surface /	terminal to terminal		2.7			mm
d _{Spb/Apb}	striking distance through air	terminal to backside		4.1			mm
V _{ISOL}	isolation voltage	t = 1 second	50/60 Hz; RMS; I _{ISOL} < 1 mA		3600		V
		t = 1 minute			3000		V

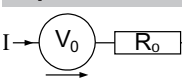
Product Marking



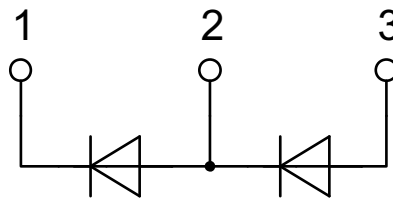
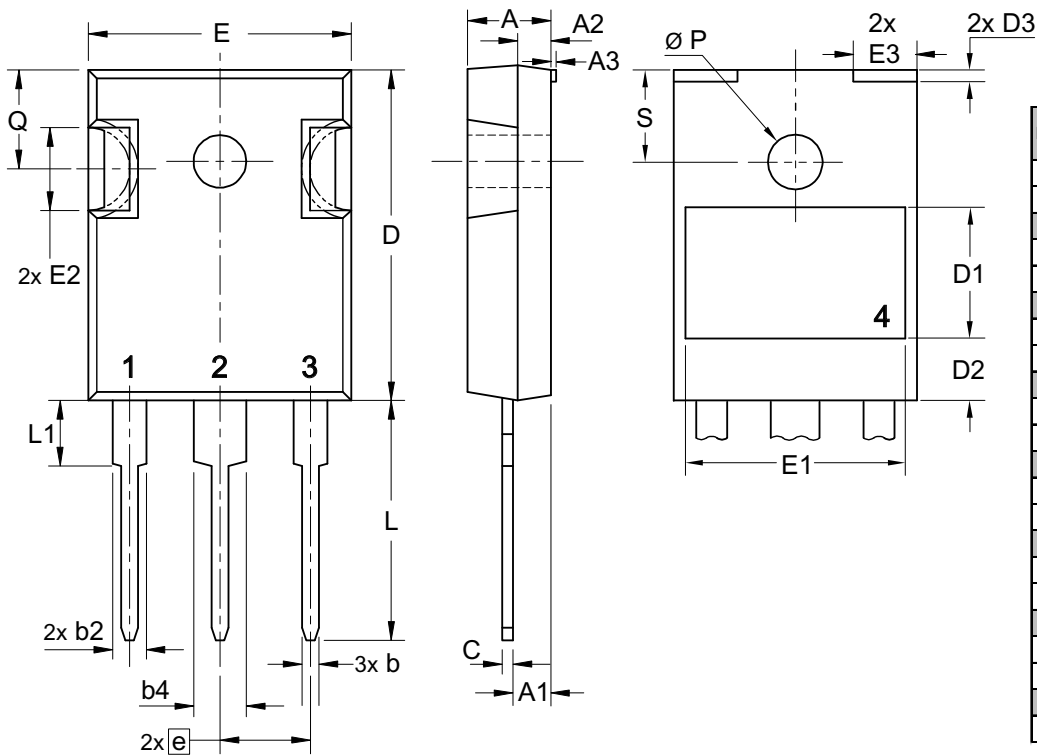
Part description

D = Diode
 C = SiC
 G = Extreme fast
 10 = Current Rating [A]
 P = Phase leg
 1200 = Reverse Voltage [V]
 HR = ISO247 (3)

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	DCG10P1200HR	DCG10P1200HR	Tube	30	DCG10P1200HR

Equivalent Circuits for Simulation		*on die level, typical		
		$T_{VJ} = 125^{\circ}\text{C}$	$T_{VJ} = 175^{\circ}\text{C}$	
$V_{0\max}$	threshold voltage	0.77	0.68	V
$R_{0\max}$	slope resistance *	107	133	mΩ

Outlines ISO247



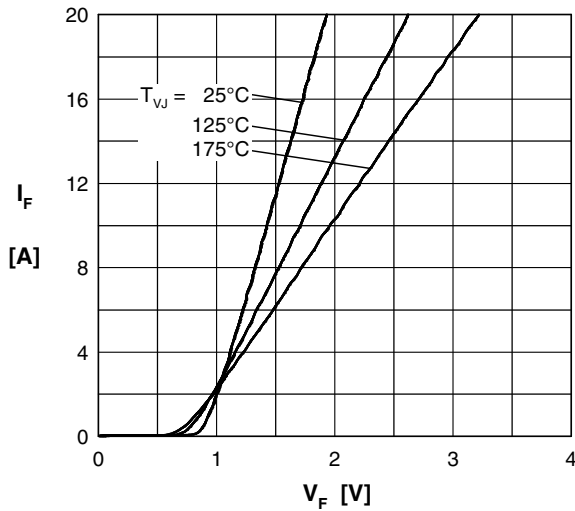
SiC Diode (per diode)


Fig. 1 Typ. forward characteristics.

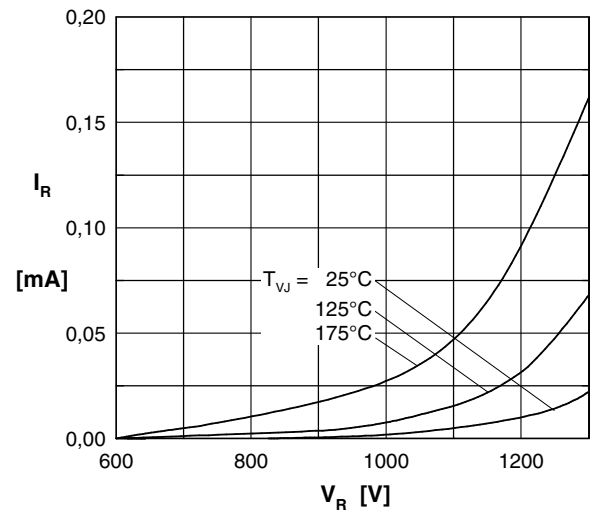


Fig. 2 Typ. reverse characteristics

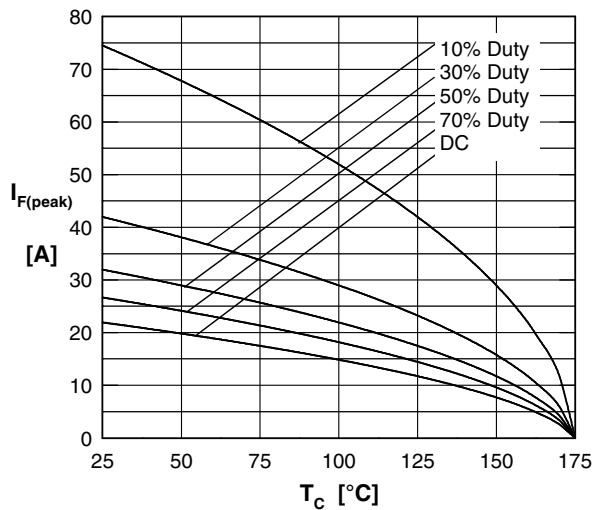


Fig. 3 Typ. current derating

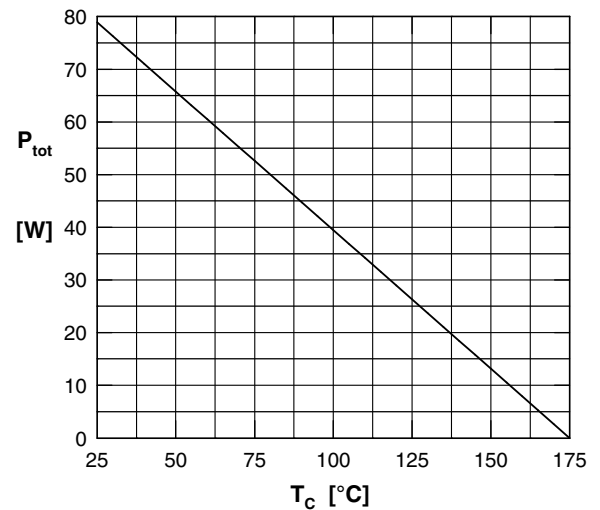


Fig. 4 Power derating

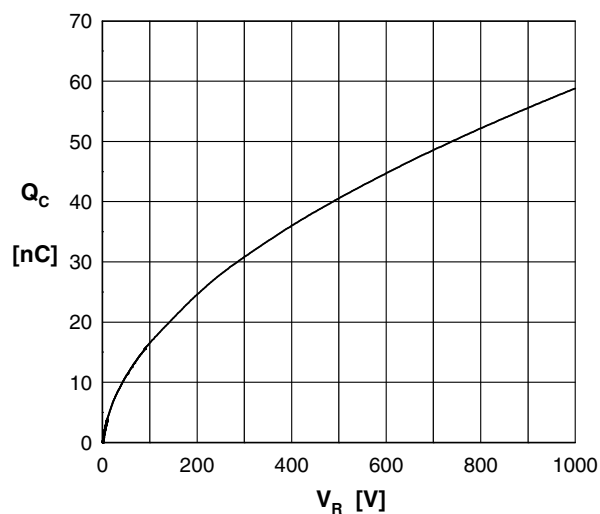


Fig. 5 Typ. recovery charge vs. reverse voltage

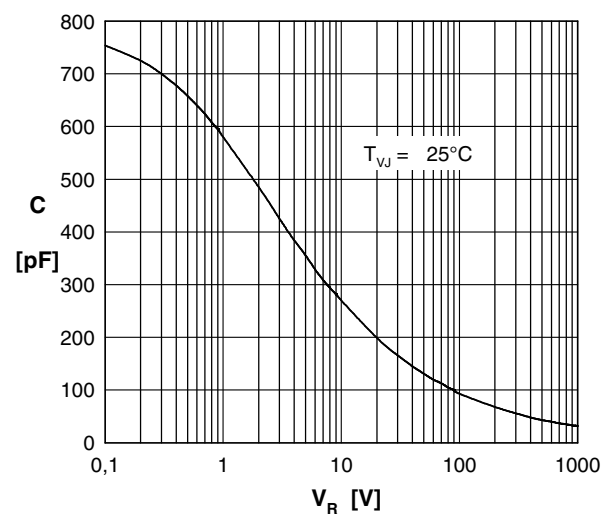


Fig. 6 Typ. junction capacitance vs. reverse Voltage

SiC Diode (per diode)

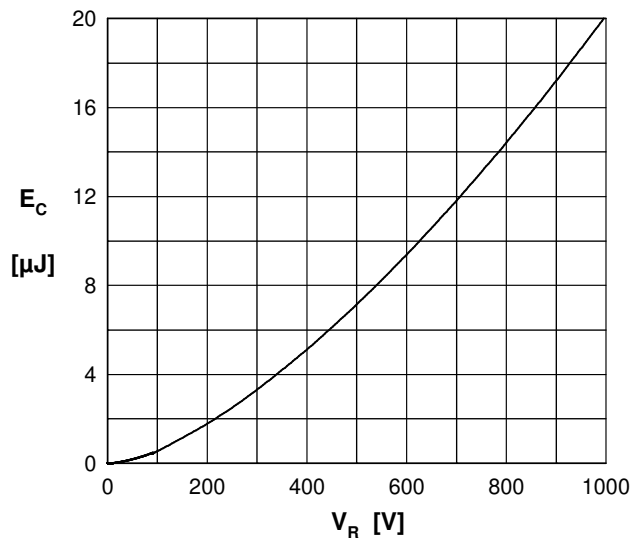


Fig. 7 Typical capacitance stored energy

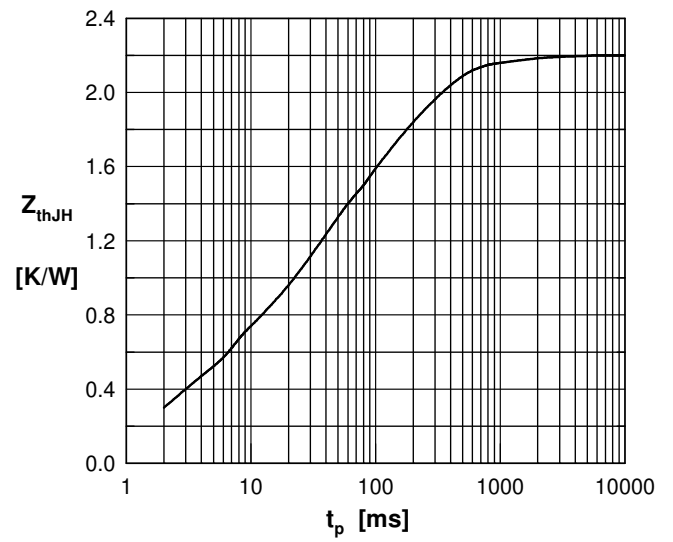


Fig. 8 Typ. transient thermal impedance junction to heatsink